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Date : June 21, 2005

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Patent No: 6806109 B2
Applicant: Hiroyuki Furuya, et al.
Issued: October 19, 2004
Title: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD
OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

Request for Certificate of Correction:

Consideration had been given to your request for the issuance of a certificate of correction for the above-identified patent under the provisions of Rule 1.322.

Respecting the alleged error under Foreign Patent Documents, the patent is printer in accordance with the record, since the references was not in conformance and not considered. Therefore, no correction is in order here under 1.322 or 1.323.

In view of the foregoing, your request in this matter is hereby **denied**.

A certificate of correction will be issued to correct the remaining error mentioned in your request.

Correspondence concerning this matter should be filed and directed to Decisions and Certificate of Correction Branch.

Virginia Tolbert
For Cecelia Newman, Supervisor
Decisions and Certificate of Correction
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